Doc No. TT4-EA-12653

Revision. 3

MOS FET

FJ3303010L

Panasonic

FJ3303010L

Silicon P-channel MOSFET

For switching FJ350301 in SSSMini3 type package

■ Features

 Low drive voltage: 2.5 V drive
 Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)

■ Marking Symbol: U1

Established: 2010-06-25

: 2013-10-10

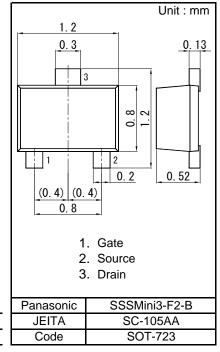
Revised

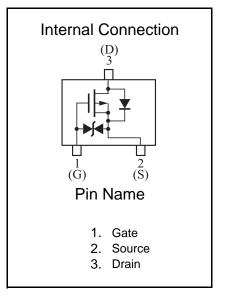
■ Packaging

Embossed type (Thermo-compression sealing) :10 000 pcs / reel (standard)

■ Absolute Maximum Ratings Ta = 25 °C

Parameter	Symbol	Rating	Unit
Drain-source voltage	VDS	-30	V
Gate-source voltage	VGS	±12	V
Drain current	ID	-100	mA
Pulse drain current	IDp	-200	mA
Total power dissipation	PD	100	mW
Channel temperature	Tch	150	
Operating ambient temperature	Topr	-40 to +85	°C
Storage temperature	Tstg	-55 to +150	





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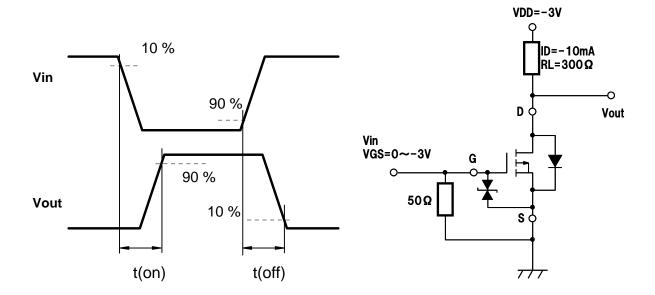
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■ Electrical Characteristics Ta = 25 °C ± 3 °C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Drain-source breakdown voltage	VDSS	ID = -1 mA, VGS = 0	-30			V
Drain-source cutoff current	IDSS	VDS = -30 V, VGS = 0			-1.0	μΑ
Gate-source cutoff current	IGSS	$VGS = \pm 10 \text{ V}, VDS = 0$			±10	μΑ
Gate threshold voltage	VTH	ID = -1.0 μ A, VDS = -3.0 V	-0.5	-1.0	-1.5	V
Drain-source ON resistance	RDS(on)1	ID = -10 mA, VGS = -2.5 V		7	17	Ω
	RDS(on)2	ID = -10 mA, VGS = -4.0 V		4	7	Ω
Forward transfer admittance	Yfs	ID = -10 mA, VDS = -3.0 V	20	40		mS
Input capacitance	Ciss			12		pF
Output capacitance	Coss	VDS = -3 V, $VGS = 0$, $f = 1 MHz$		7		pF
Reverse transfer capacitance	Crss			3		pF
Turn-on time ^{*1}	ton	VDD = -3 V, VGS = 0 to -3 V		100		ns
		ID = -10 mA		. 50		
Turn-off time *1	toff	VDD = -3 V, $VGS = -3 to 0 V$		100		ns
		ID = -10 mA				

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

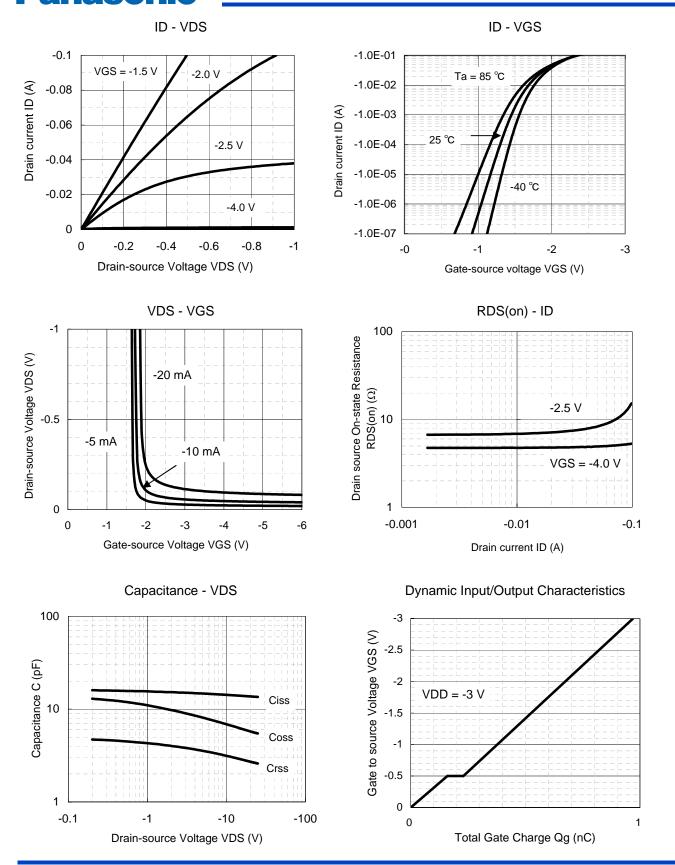
2. *1 Turn-on and Turn-off test circuit



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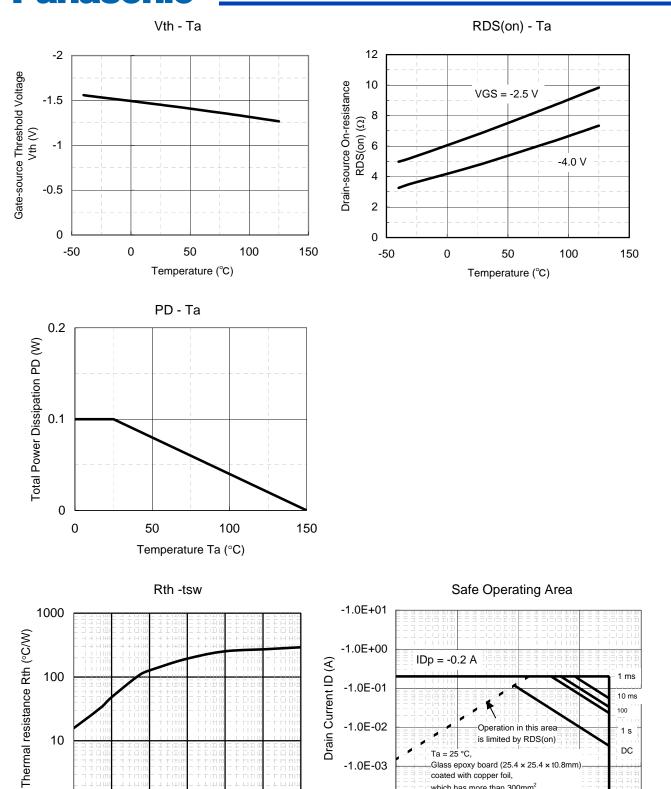
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-1.0E-03

-1.0E-04

-0.01

100

1000

Glass epoxy board (25.4 x 25.4 x t0.8mm)

Drain-source Voltage VDS (V)

coated with copper foil, which has more than 300mm²

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-100

-10

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0.001 0.01

0.1

1

Pulse Width tsw (s)

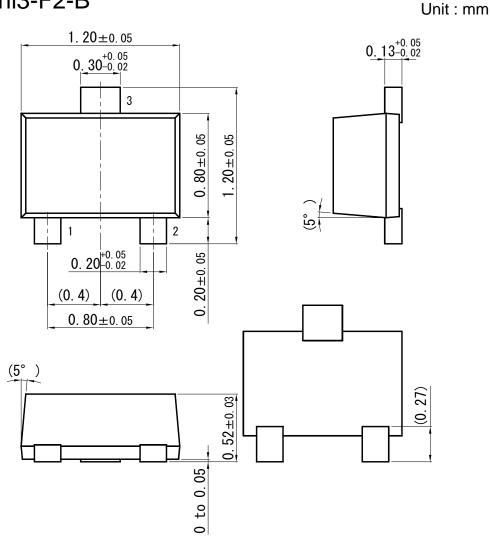
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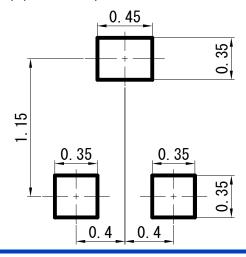
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SSSMini3-F2-B



■ Land Pattern (Reference) (Unit: mm)



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